

# FS5ASJ-3

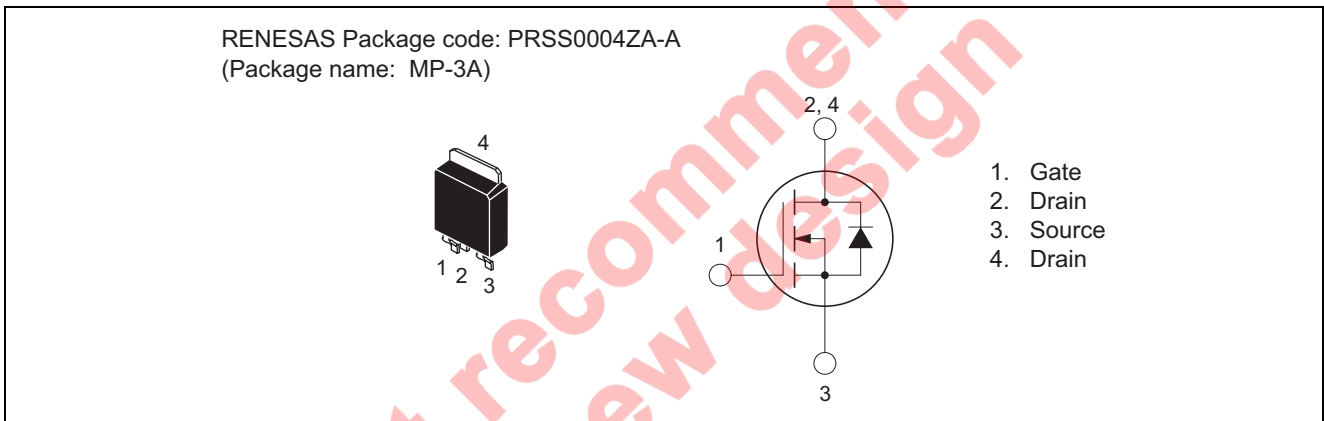
High-Speed Switching Use  
Nch Power MOS FET

REJ03G1406-0200  
(Previous: MEJ02G0077-0101)  
Rev.2.00  
Aug 07, 2006

## Features

- Drive voltage : 4 V
- $V_{DSS}$  : 150 V
- $r_{DS(ON) (max)}$  : 0.35  $\Omega$
- $I_D$  : 5 A
- Integrated Fast Recovery Diode (TYP.) : 85 ns

## Outline



## Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

## Maximum Ratings

( $T_c = 25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	$V_{DSS}$	150	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	$V_{GSS}$	$\pm 20$	V	$V_{DS} = 0\text{ V}$
Drain current	$I_D$	5	A	
Drain current (Pulsed)	$I_{DM}$	20	A	
Avalanche drain current (Pulsed)	$I_{DA}$	5	A	$L = 100\ \mu\text{H}$
Source current	$I_S$	5	A	
Source current (Pulsed)	$I_{SM}$	20	A	
Maximum power dissipation	$P_D$	30	W	
Channel temperature	$T_{ch}$	- 55 to +150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 55 to +150	$^\circ\text{C}$	
Mass	—	0.32	g	Typical value

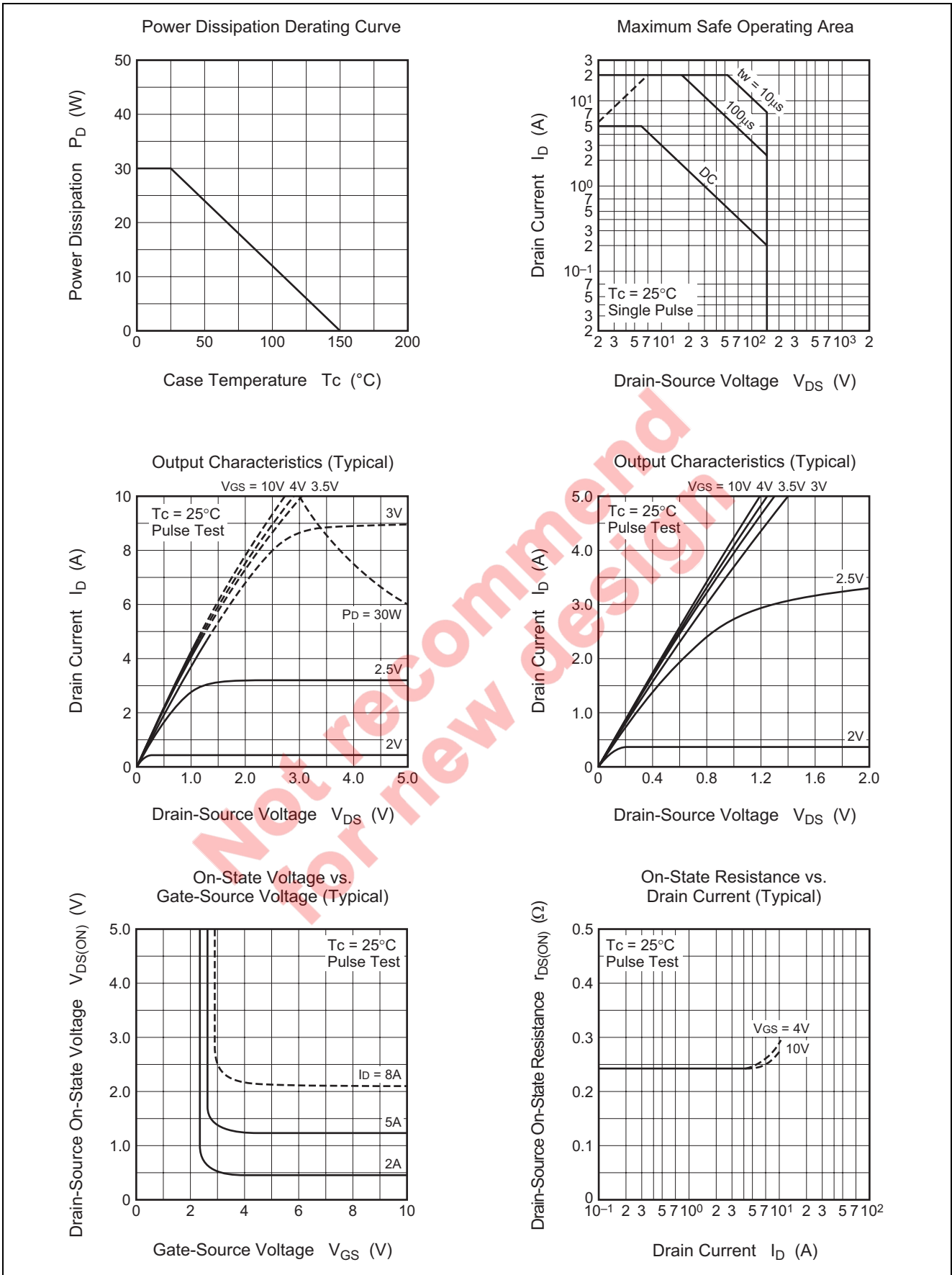
## Electrical Characteristics

(T<sub>ch</sub> = 25°C)

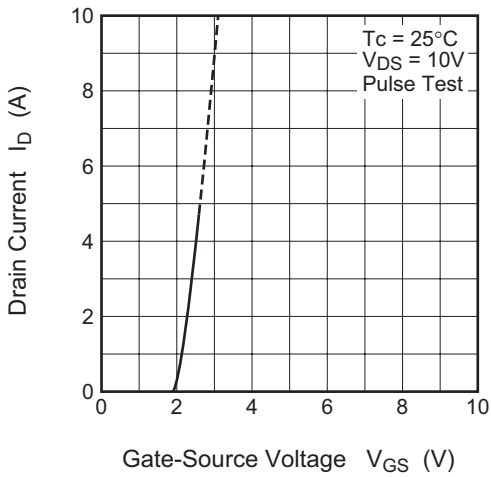
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	150	—	—	V	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V
Gate-source leakage current	I <sub>GSS</sub>	—	—	±0.1	μA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Drain-source leakage current	I <sub>DSS</sub>	—	—	0.1	mA	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V
Gate-source threshold voltage	V <sub>GS(th)</sub>	1.0	1.5	2.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.27	0.35	Ω	I <sub>D</sub> = 2 A, V <sub>GS</sub> = 10 V
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.28	0.37	Ω	I <sub>D</sub> = 2 A, V <sub>GS</sub> = 4 V
Drain-source on-state voltage	V <sub>DS(ON)</sub>	—	0.54	0.70	V	I <sub>D</sub> = 2 A, V <sub>GS</sub> = 10 V
Forward transfer admittance	y <sub>fs</sub>	—	9.5	—	S	I <sub>D</sub> = 2 A, V <sub>DS</sub> = 5 V
Input capacitance	C <sub>iss</sub>	—	800	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1MHz
Output capacitance	C <sub>oss</sub>	—	100	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	35	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	14	—	ns	V <sub>DD</sub> = 80 V, I <sub>D</sub> = 2 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = R <sub>GS</sub> = 50 Ω
Rise time	t <sub>r</sub>	—	17	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	65	—	ns	
Fall time	t <sub>f</sub>	—	31	—	ns	
Source-drain voltage	V <sub>SD</sub>	—	1.0	1.5	V	I <sub>S</sub> = 2 A, V <sub>GS</sub> = 0 V
Thermal resistance	R <sub>th(ch-c)</sub>	—	—	4.17	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	—	85	—	ns	I <sub>S</sub> = 5 A, d <sub>is</sub> /d <sub>t</sub> = -100 A/μs

Not recommended  
for new designs

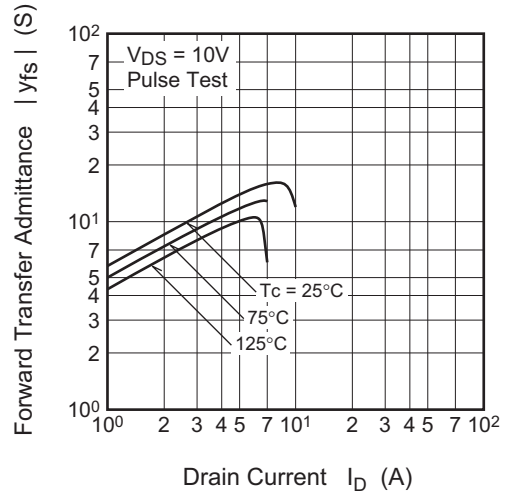
Performance Curves



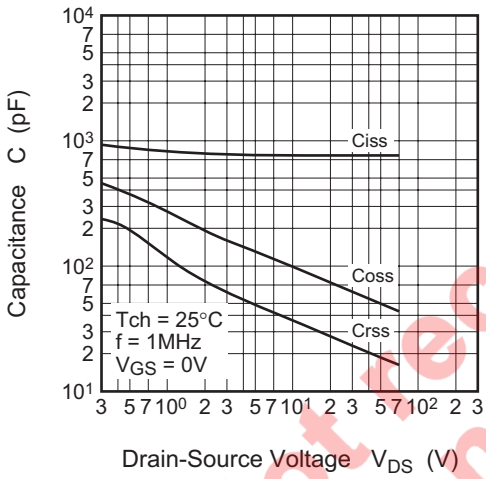
Transfer Characteristics (Typical)



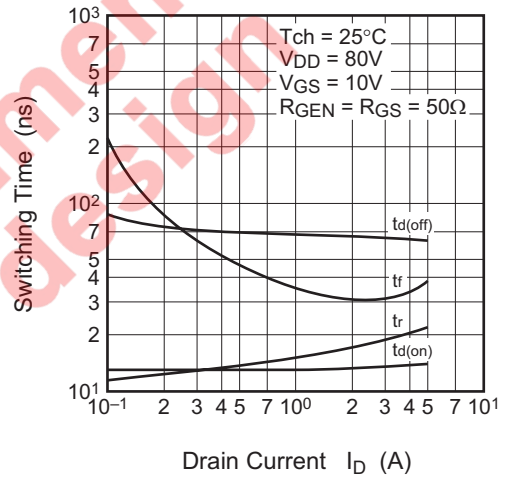
Forward Transfer Admittance vs. Drain Current (Typical)



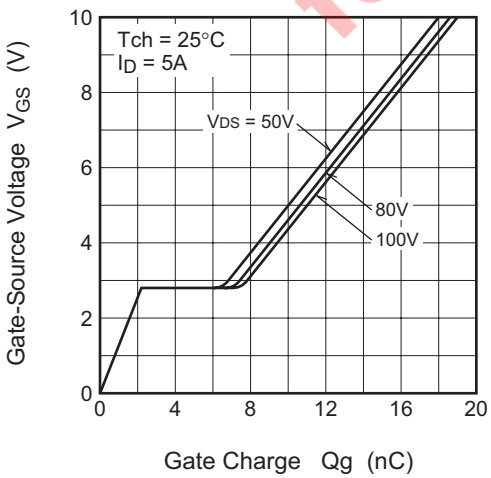
Capacitance vs. Drain-Source Voltage (Typical)



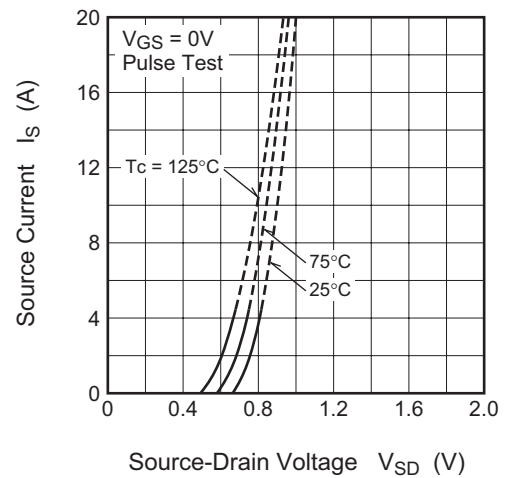
Switching Characteristics (Typical)

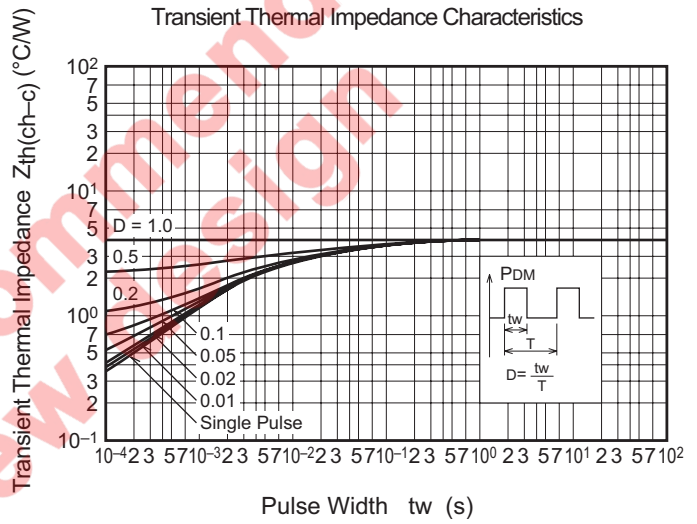
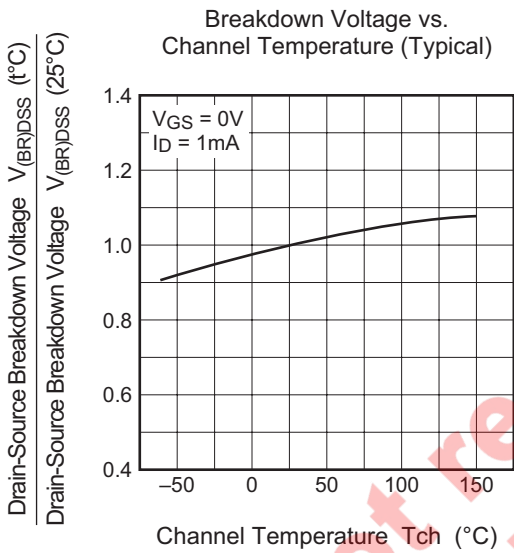
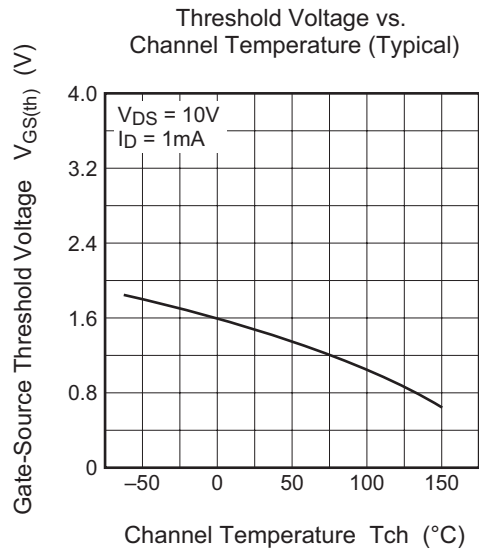
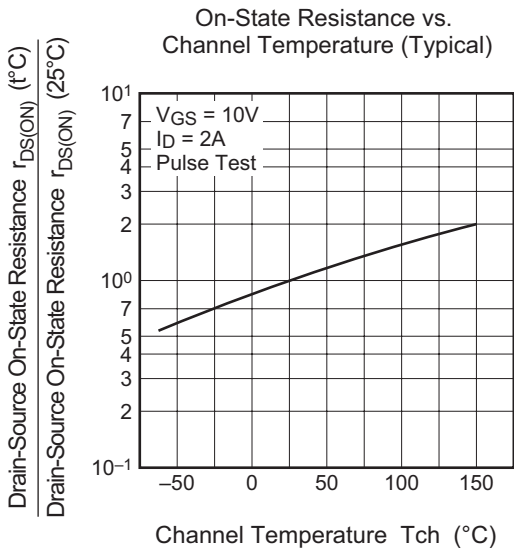


Gate-Source Voltage vs. Gate Charge (Typical)

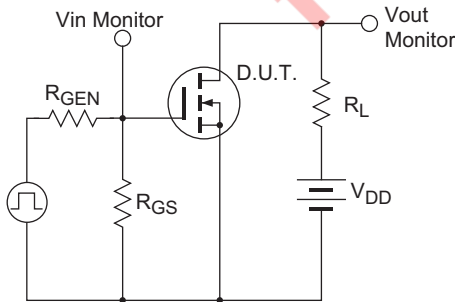


Source-Drain Diode Forward Characteristics (Typical)

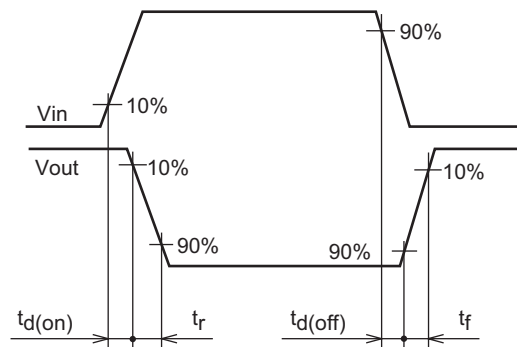




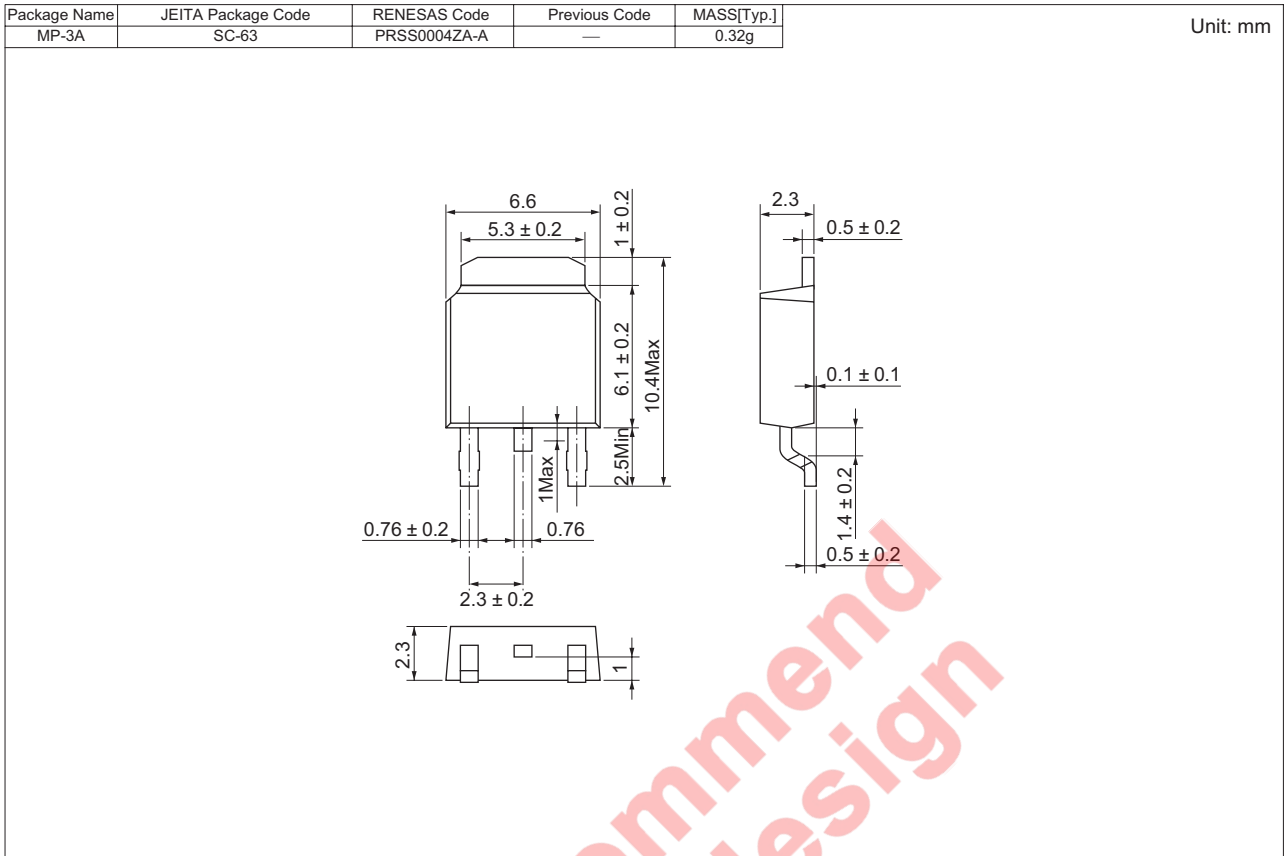
Switching Time Measurement Circuit



Switching Waveform



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS5ASJ-3-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS5ASJ-3

Note : Please confirm the specification about the shipping in detail.

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